



INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

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Application Number

09/886,823

Applicant(s)

Bryant et al.

Filing Date

06/21/01

Group Art Unit

2826

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
ftj		5,899,710	05/04/99	Mukai	438	156	
↓		6,197,672	03/06/01	Lin et al.	438	592	

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
ftj		EP 0 694 977 A2	01/31/96	European (DE, FR, GB, NL)				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

ftj		Kim K et al., "Double-Gate CMOS: Symmetrical-Versus Asymmetrical-Gate Devices" IEEE Transactions on Electron Devices, IEEE Inc. New York, US, vol. 48, no. 2, February 2001 (2001-02), pages 294-299, XP001038978, ISSN: 0018-9383

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.